



Low-Voltage Single SPDT Analog Switch

DESCRIPTION

The DG2002 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 8 ns, t_{OFF} : 6 ns), low on-resistance ($r_{DS(on)}$: 7 Ω) and small physical size (SC70), the DG2002 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG2002 is built on Vishay Siliconix's low voltage JI2 process. An epitaxial layer prevents latchup. Break-before make is guaranteed for DG2002.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FEATURES

- Low voltage operation (1.8 V to 5.5 V)
- Low on-resistance $r_{DS(on)}$: 7 Ω
- Fast switching t_{ON}: 8 ns, t_{OFF}: 6 ns
- Low charge injection Q_{INJ}: 5 pC
- Low power consumption
- TTL/CMOS compatible
- 6-pin SC70 package

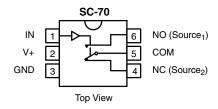
BENEFITS

- · Reduced power consumption
- Simple logic interface
- High accuracy
- · Reduce board space

APPLICATIONS

- · Cellular phones
- · Communication systems
- · Portable test equipment
- · Battery operated systems
- · Sample and hold circuits

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device Marking: E2xx

TRUTH TABLE						
Logic	NC	NO				
0	ON	OFF				
1	OFF	ON				

ORDERING INFORMATION						
Temp Range	Package	Part Number				
- 40 to 85 °C	SC70-6	DG2002DL-T1 DG2002DL-T1-E3				

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^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.



ABSOLUTE MAXIMUM RATINGS						
Parameter		Limit	Unit			
Referenced V+ to GND		- 0.3 to +6	V			
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3				
Continuous Current (Any Terminal)		± 50	mA			
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 200	IIIA			
Storage Temperature		- 65 to + 150	°C			
Power Dissipation (Packages) ^b	6-Pin SC70 ^c	250	mW			

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC Board.
- c. Derate 3.1 mW/°C above 70 °C.

SPECIFICATIONS V	+ = 2.0 V							
		Test Conditions Unless Otherwise Specified V+ = 2.0 V, ± 10 %		Limits - 40 to 85 °C			-	
Parameter	Symbol	$V_{IN} = 0.4 \text{ or } 1.6 \text{ V}^{e}$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit	
Analog Switch								
Analog Signal Range ^d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0		V+	V	
On-Resistance	r _{ON}	$V+ = 1.8 \text{ V}, V_{COM} = 1.0 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full ^d		38 39.3	46.1 47.1	Ω	
r _{ON} Flatness ^d	r _{ON} Flatness	$V+ = 1.8 \text{ V}, V_{COM} = 0 \text{ to } V+, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		21		22	
Cuitab Off Lackage Current	I _{NO(off)} I _{NC(off)}	V+ = 2.2 V	Room Full ^d	- 250 - 3.0		250 3.0	pA nA	
Switch Off Leakage Current ^f	I _{COM(off)}	V_{NO} , $V_{NC} = 0.5 \text{ V/1.5 V}$, $V_{COM} = 1.5 \text{ V/0.5 V}$	Room Full ^d	- 250 - 3.0		250 3.0	pA nA	
Channel-On Leakage Current ^f	I _{COM(on)}	$V+ = 2.2 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.5 \text{ V}/1.5 \text{ V}$	Room Full ^d	- 250 - 3.0		250 3.0	pA nA	
Digital Control			•					
Input High Voltage	V_{INH}		Full	1.6			V	
Input Low Voltage	V _{INL}		Full			0.4	V	
Input Capacitance ^d	C _{in}		Full		3		pF	
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ	
Dynamic Characteristics								
Turn-On Time	t _{ON}	VV 45V.D 200.0.0 25v.F	Room Full ^d		22	31 32		
Turn-Off Time	t _{OFF}	V_{NO} or V_{NC} = 1.5 V, R_L = 300 Ω , C_L = 35 pF Figures 1 and 2	Room Full ^d		10	17 18	ns	
Break-Before-Make Time	t _d		Room	1	12			
Charge Injection ^d	Q_{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	рC	
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 1 MHz$	Room		- 67		40	
Crosstalk ^d	X _{TALK}	$n_L = 30.22$, $o_L = 3 \text{ pr}$, $i = 1 \text{ M/nZ}$	Room		- 71		dB	
NO, NC Off Capacitance ^d	$C_{NO(off)} \ C_{NC(off)}$	V _{IN} = 0 or V+, f = 1 MHz	Room		5		pF	
Channel-On Capacitanced	C _{ON}		Room		29			
Power Supply	1				1			
Power Supply Range	V+			1.8		2.2	V	
Power Supply Current ^d	I+	V _{IN} = 0 or V+		_	0.01	1.0	μΑ	
Power Consumption	P _C	VIN - O OI VT				2.2	μW	





SPECIFICATIONS V-	_ U.U V	Test Conditions			Limits		
		Unless Otherwise Specified V+ = 3 V, ±10 %		- 40 to 85 °C			
Parameter	Symbol	$V_{IN} = 0.4 \text{ or } 2.0 \text{ V}^{e}$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit
Analog Switch			•				
Analog Signal Range ^d	$V_{NO}, V_{NC} V_{COM}$		Full	0		V+	V
On-Resistance ^d	r _{ON}	$V+ = 2.7 \text{ V}, V_{COM} = 1.5 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full		12.2 13	14.8 15.8	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	$V+ = 2.7 \text{ V}, V_{COM} = 0 \text{ to } V+, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		5		52
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V	Room Full	- 500 - 4.0		500 4.0	pA nA
Switch On Leakage Current	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V/3 V}$, $V_{COM} = 3 \text{ V/1 V}$	Room Full	- 500 - 4.0		500 4.0	pA nA
Channel-On Leakage Current ^f	I _{COM(on)}	$V+ = 3.3 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 1 \text{ V/3 V}$	Room Full	- 500 - 4.0		500 4.0	pA nA
Digital Control			•				
Input High Voltage	V _{INH}		Full	2			V
Input Low Voltage	V _{INL}		Full			0.4	V
Input Capacitance ^d	C _{in}		Full		3		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ
Dynamic Characteristics							
Turn-On Time ^d	t _{ON}	V_{NO} or V_{NC} = 2.0 V, R_L = 300 Ω , C_L = 35 pF	Room Full		12	21 22	
Turn-Off Time ^d	t _{OFF}	Figures 1 and 2	Room Full		7	14 15	ns
Break-Before-Make Time ^d	t _d		Room	1	6		
Charge Injection ^d	Q_{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		5	10	рC
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room		- 67		dB
Crosstalk ^d	X _{TALK}	11 = 30 12, 0 = 3 μ1, 1 = 1 101112	Room		- 69		uБ
NO, NC Off Capacitance ^d	$C_{NO(off)} \ C_{NC(off)}$	V _{IN} = 0 or V+, f = 1 MHz	Room		5		pF
Channel-On Capacitance ^d	C _{ON}		Room		29		
Power Supply							
Power Supply Range	V+			2.7		3.3	V
Power Supply Current	l+	V _{IN} = 0 or V+			0.01	1.0	μΑ
Power Consumption	P _C	- 111				3.3	μW



SPECIFICATIONS V	- = 5.0 V							
		Test Conditions Unless Otherwise Specified V+ = 5 V, ± 10 %		-		Limits - 40 to 85 °C		
Parameter	Symbol	$V_{IN} = 0.8 \text{ or } 2.4 \text{ V}^{e}$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit	
Analog Switch								
Analog Signal Range ^d	$V_{NO}, V_{NC,} V_{COM}$		Full	0		V+	V	
On-Resistance	r _{ON}	$V+ = 4.5 \text{ V}, V_{COM} = 3 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full		6.4 7.4	7.8 8.8	Ω	
r _{ON} Flatness ^d	r _{ON} Flatness	$V+ = 4.5 \text{ V}, V_{COM} = 0 \text{ to } V+, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		3		52	
Switch Off Leakage Current	I _{NO(off),} I _{NC(off)}	V+ = 5.5 V	Room Full	- 1.0 - 4.0		1.0 4.0		
Switch On Leakage Ourient	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V}/4.5 \text{ V}$, $V_{COM} = 4.5 \text{ V}/1 \text{ V}$	Room Full	- 1.0 - 4.0		1.0 4.0	nA	
Channel-On Leakage Current	I _{COM(on)}	V+ = 5.5 V, V+ = 5.5 V $V_{NO}, V_{NC} = V_{COM} = 1 V/4.5 V$	Room Full	- 1.0 - 4.0		1.0 4.0		
Digital Control				<u> </u>		<u> </u>	I	
Input High Voltage	V_{INH}		Full	2.4			W	
Input Low Voltage	V_{INL}		Full			0.8	V	
Input Capacitance	C _{in}		Full		3		pF	
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ	
Dynamic Characteristics			•		•			
Turn-On Time ^d	t _{ON}	V 20 V D 200 O C 25 pF	Room Full		8	15 16		
Turn-Off Time ^d	t _{OFF}	V_{NO} or V_{NC} = 3 V, R_L = 300 Ω , C_L = 35 pF Figures 1 and 2	Room Full		6	13 14	ns	
Break-Before-Make Time ^d	t _d		Room	1	4			
Charge Injection ^d	Q_{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ Figure 3}$	Room		5	10	рC	
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 1 MHz$	Room		- 69		40	
Crosstalk ^d	X _{TALK}	$n_L = 50.52$, $O_L = 5 \text{ pr}$, $I = 1 \text{ IM} \cdot 12$	Room		- 69		dB	
Source-Off Capacitance ^d	C _{NO(off)} , C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz	Room		5		pF	
Channel-On Capacitance ^d	C _{ON}		Room		29			
Power Supply							1	
Power Supply Range	V+			4.5		5.5	V	
Power Supply Current	l+	V _{IN} = 0 or V+			0.01	1.0	μΑ	
Power Consumption	P_{C}	*IN = 0 01 *+				5.5	μW	

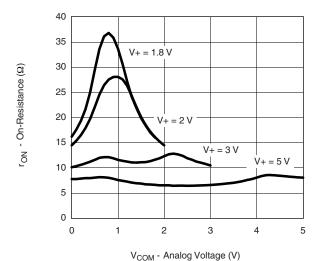
Notes:

- a. Room = 25 °C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Guaranteed by 5 V leakage testing, not production tested.

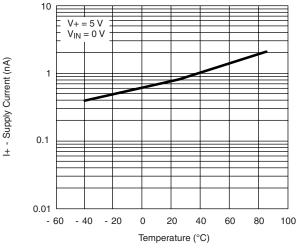
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



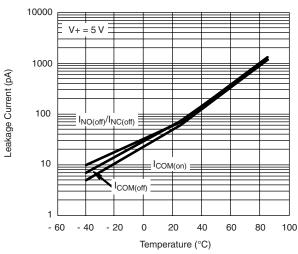
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



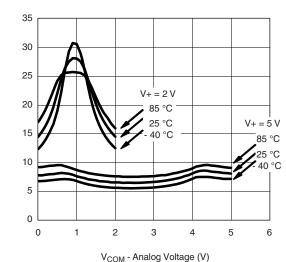
r_{ON} vs. V_{COM} and Supply Voltage



Supply Current vs. Temperature



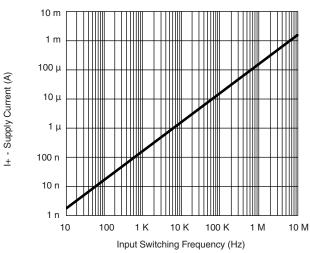
Leakage Current vs. Temperature



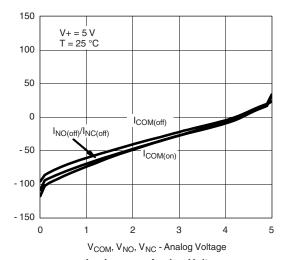
 r_{ON} - On-Resistance (Ω)

Leakage Current (pA)

r_{ON} vs. Analog Voltage and Temperature

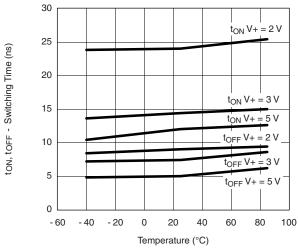


Supply Current vs. Input Switching Frequency

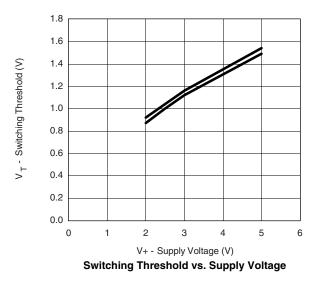


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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

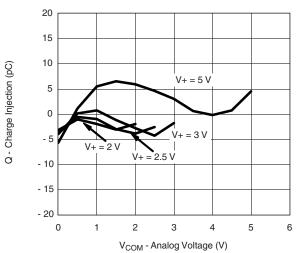


Switching Time vs. Temperature and Supply Voltage



0 LOSS - 10 - 20 Loss, OIRR, X_{TALK} (dB) - 30 - 40 - 50 - 60 - 70 $R_L = 50 \Omega$ - 80 - 90 - 100 100 K 1 M 10 M 100 M 1 G Frequency (Hz)

Insertion Loss, Off -Isolation Crosstalk vs. Frequency





TEST CIRCUITS

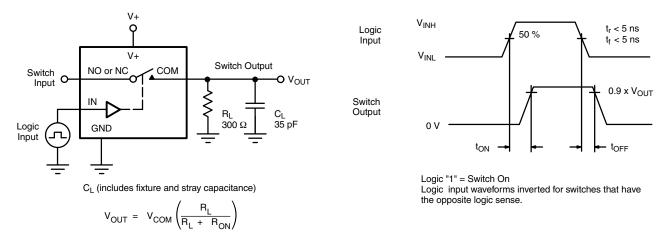


Figure 1. Switching Time

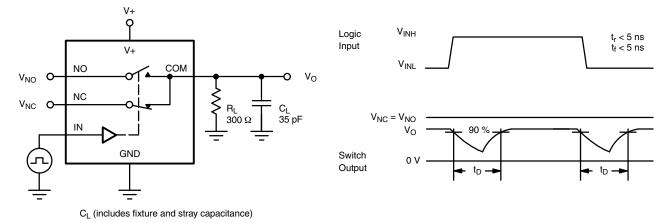


Figure 2. Break-Before-Make Interval

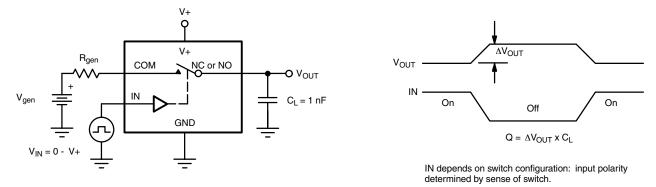


Figure 3. Charge Injection

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TEST CIRCUITS

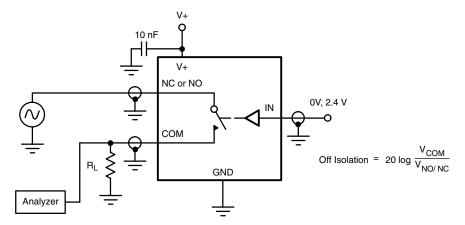


Figure 4. Off-Isolation

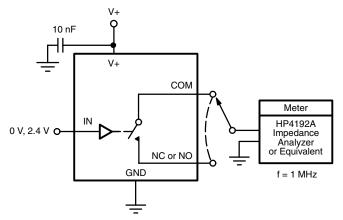


Figure 5. Channel Off/On Capacitance

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SC-70: 6-LEADS





	MIL	LIMET	ERS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.90	-	1.10	0.035	_	0.043	
A ₁	-	-	0.10	-	-	0.004	
A_2	0.80	-	1.00	0.031	-	0.039	
b	0.15	-	0.30	0.006	_	0.012	
С	0.10	-	0.25	0.004	_	0.010	
D	1.80	2.00	2.20	0.071	0.079	0.087	
Ε	1.80	2.10	2.40	0.071	0.083	0.094	
E ₁	1.15	1.25	1.35	0.045	0.049	0.053	
е	0.65BSC			0.026BSC			
e ₁	1.20	1.30	1.40	0.047	0.051	0.055	
L	0.10	0.20	0.30	0.004	0.008	0.012	
9		7°Nom			7°Nom		



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